



TO-9 Packaged Laser Diode

High Power Single-Mode and Multi-Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available

ApplicationsOEM MedicalProfessional Medical

Lensed Options Available

- LiDAR
 Military / Aerospace
 Illumination

Features

- Cost effective
- High Output Power
- High Dynamic Range
- High Efficiency .
- Standard Low Cost Package

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.



2.6 5 180um Power 2.4 4.5 2.2 4 2 95um Power 50um Power 1.8 3.5 Optical Power [W] 3 Ê 2.5 Voltage 2 0.8 1.5 0.6 Voltage 1 0.4 0.5 0.2 0 0 0 2 4 8 10 12 14 6 Current [A]

TO9: 1550nm 2.5mm CL, Uncapped



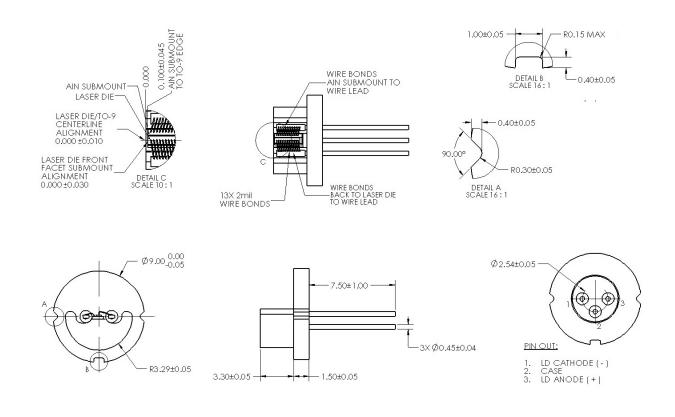




| om | Nex | |
|-------|--------|--|
| LASER | DIODES | |
| | | |
| | | |

| | Symbol | TO9-116 | Units |
|-----------------------|-----------------|-----------|--------------|
| Optical | | | |
| Wavelength | λ _c | 1575 | nm (±20) |
| Output Power (CW) | P° | 1.60 | watts (±10%) |
| Chip Cavity Length | CL | 2500 | μm |
| Emitter Width | W | 95 | μm |
| Emitter Height | Н | 1 | μm |
| Spectral Width | δλ | 10 | nm 3dB |
| Slope Efficiency | η° | 0.30 | W/A |
| Fast Axis Div.* | ⊖_perp | 28 | deg FWHM |
| Slow Axis Div. | O_parallel | 9 | deg FWHM |
| Electrical | | | |
| Power Conversion Eff. | η | 12 | % |
| Operating Current | I _{op} | 8 | A |
| Threshold Current | I _{th} | 0.5 | A |
| Operating Voltage | V _{op} | 1.7 | V |
| Mechanical | | | |
| Weight | | 1.5 | g |
| Operating Temp.** | | -40 to 60 | °C |
| Storage Temp. | | -40 to 80 | °C |

Specified values are rated at a constant heat sink temperature of 20°C. **Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal. Uncapped T09 specifications assume heatsinking underneath laser chip. Capped T09 specifications assume heatsinking only on flat surface where pins extend.



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DANGER SIBLE / INVISIBLE LASER RADIATI CLASS IIIb and IV LASER PRODUCTS This product of the fest station. Laser radiation from this product is considered an acute hazard to the skin and eyes.